

**IN THE SPECIFICATION**

Please replace the abstract with the new abstract attached hereto.

**REPLACEMENT SHEET**

--A field effect transistor and method for making is described incorporating self aligned source ~~and~~ and drain contacts with Schottky metal-to-semiconductor junction and a T-shaped gate or incorporating highly doped semiconductor material for the source and drain contacts different from the channel material to provide etch selectivity and a T-shaped gate or incorporating a metal for the source and drain contacts and the oxide of the metal for the gate dielectric which is self aligned.--